

MEMC 98-3052 (2512.2)
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster
Serial No. 10/038,084
Filed January 03, 2002
Confirmation No. 7363

Art Unit 2814

For SILICON ON INSULATOR STRUCTURE HAVING A LOW DEFECT DENSITY
DEVICE LAYER AND A PROCESS FOR THE PREPARATION THEREOF

Examiner Anh D. Mai

August 27, 2004

AMENDMENT D

TO THE COMMISSIONER FOR PATENTS,

SIR:

In response to Telephone Interview of today, August 27, 2004, please consider
the following amendments and remarks:

Amendments begin on page 2 of this paper,

Remarks/Arguments begin on page 5 of this paper.

Law Offices of

SENNIGER POWERS

One Metropolitan Square, 16th Floor
St. Louis, Missouri 63102

Telephone (314) 231-5400
Facsimile (314) 231-4342

FACSIMILE TRANSMITTAL COVER SHEET

DATE: August 27, 2004 ATTORNEY DOCKET NUMBER: MEMC 98-3005 (2512.2)
PTO FACSIMILE NUMBER: (571) 273-1710

PLEASE DELIVER THIS FACSIMILE TO: Examiner Mai
THIS FACSIMILE IS BEING SENT BY: Richard A. Schuth
NUMBER OF PAGES: 7 INCLUDING COVER SHEET

TIME SENT: 1:55 pm OPERATOR'S NAME Sally A. Taylor

CERTIFICATION OF FACSIMILE TRANSMISSION

I hereby certify that this paper is being facsimile transmitted to
the Patent and Trademark Office on the date shown below.

Sally A. Taylor
Typed or printed name of person signing certification

 8/27/04
Signature Date

Type of paper transmitted: Amendment D

Applicant's Name: Robert J. Falster

Serial No. (Control No.): 10/038,084 Examiner: Mai

Filing Date: January 03, 2002 Art Unit: 2814

Application Title: SILICON ON INSULATOR STRUCTURE HAVING A LOW
DEFECT DENSITY DEVICE LAYER AND A PROCESS FOR THE PREPARATION
THEREOF

IF YOU DO NOT RECEIVE ALL PAGES CLEARLY, CALL BACK AS SOON AS
POSSIBLE. CONFIRMING NUMBER IS (314) 231-5400.